

### 55STS8201-VB Datasheet

### **Dual N-Channel MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
20	0.024 at V <sub>GS</sub> = 4.5 V	6.0		
	0.028 at V <sub>GS</sub> = 2.5 V	5.0		

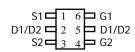
#### **FEATURES**

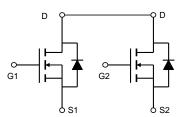
- Halogen-free Option Available
- Trench Power MOSFETs 100 %  $\rm R_{\rm g}$  Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT

TSOP6 **Top View** 





<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25$ °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
Continuous Drain Current /T 450 °C\8	T <sub>A</sub> = 25 °C	I <sub>D</sub>	6.0	5.2		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		4.8	4.2		
Pulsed Drain Current		I <sub>DM</sub>	30		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.5	1.0		
Manimum Danier Disain etian d	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.5	1.0	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] ' <sup>'</sup> D	0.96	0.64	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Manifesture Investigate As Aughtentia	t ≤ 10 s	R <sub>thJA</sub>	72	83	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	'`thJA	100	120		
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	55	70		

a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$ 

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



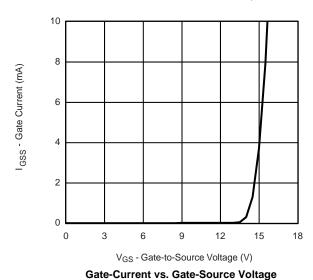
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Typ. <sup>a</sup>	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.5		1.5	V		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V		1	μA		
	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C					
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α		
5 · 6 · 6 · 6 · 6 · 6	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$		0.024	Ω			
Drain-Source On-State Resistance <sup>b</sup>		$V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A}$		0.028		22		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 5.5 \text{ A}$		30		S		
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>S</sub> = 1.5 A, V <sub>GS</sub> = 0 V		0.71	1.2	V		
Dynamic <sup>a</sup>								
Total Gate Charge	$Q_g$			12	18			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.5 \text{ A}$		2.2		nC		
Gate-Drain Charge	$Q_{gd}$			3.6				
Turn-On Delay Time	t <sub>d(on)</sub>			245	365			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		330	495			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_G$ = 6 $\Omega$		860	1300	ns		
Fall Time	t <sub>f</sub>			510	765			

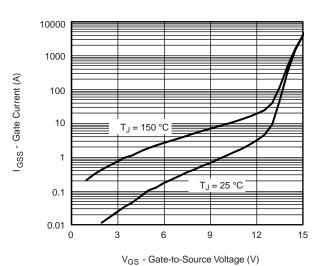
#### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

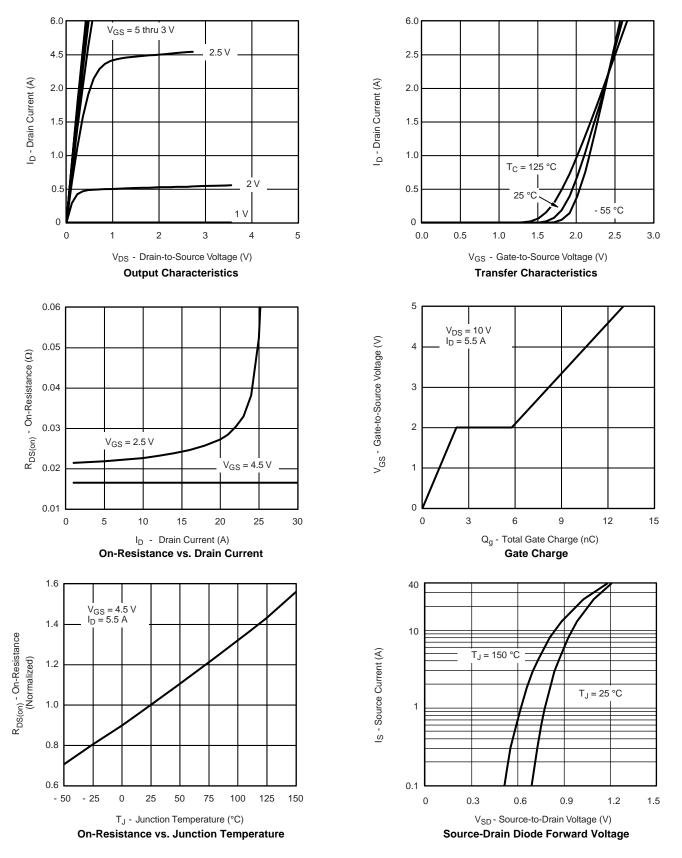




Gate Current vs. Gate-Source Voltage

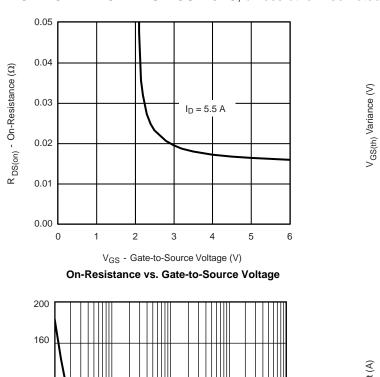


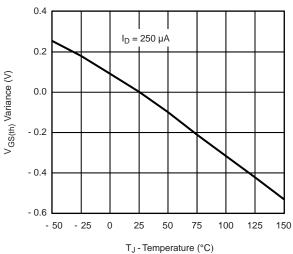
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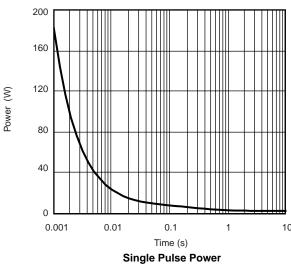


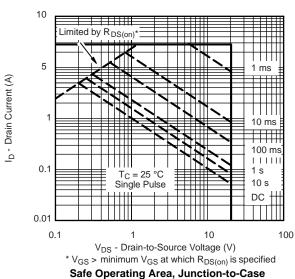
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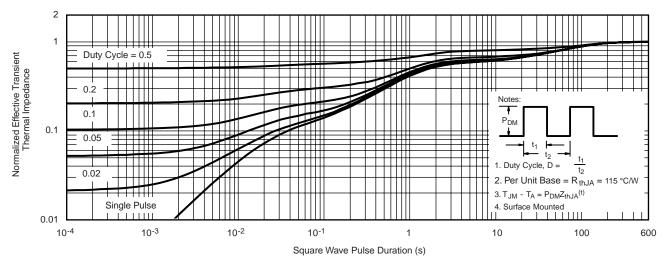




Threshold Voltage



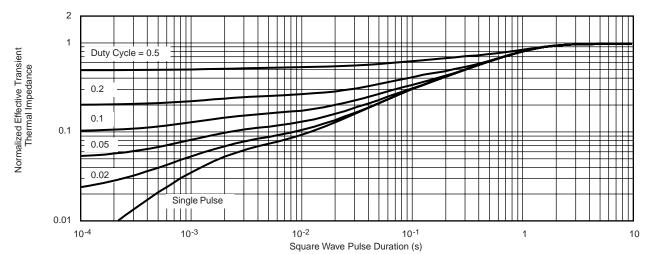




Normalized Thermal Transient Impedance, Junction-to-Ambient



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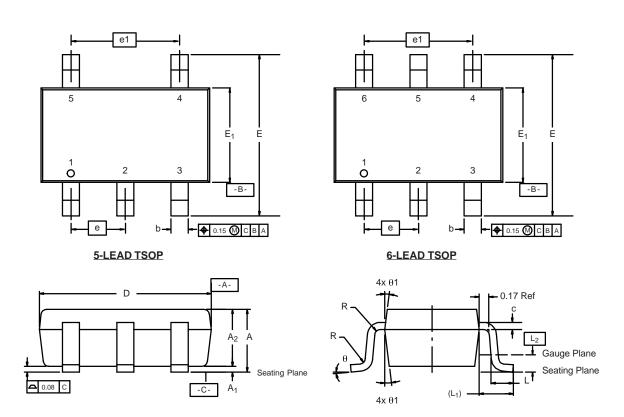


Normalized Thermal Transient Impedance, Junction-to-Foot



TSOP: 5/6-LEAD

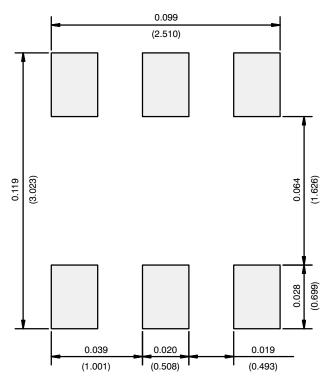
**JEDEC Part Number: MO-193C** 



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071 0.075 0		0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref			0.024 Ref			
L <sub>2</sub>	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
$\theta_1$	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



#### **RECOMMENDED MINIMUM PADS FOR TSOP-6**



Recommended Minimum Pads Dimensions in Inches/(mm)



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